

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		09/045,118	SUZUKI ET AL.	
Examiner		Art Unit		Page 1 of 1
Michelle Estrada		2823		

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,277,678	08-2001	Lee, Joo-hyung	438/151
*	B	US-5,440,157	08-1995	Imai et al.	257/310
*	C	US-6,291,366	09-2001	Sano et al.	438/773
*	D	US-5,780,908	07-1998	Sekiguchi et al.	257/383
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Sano, Naoki, et al., "High Quality SiO ₂ /Si interfaces of Poly-Crystalline Silicon thin film Transistors by Annealing in Wet Atmosphere", IEEE Electron Device Letters, Vol. 16, No. 5, May 1995.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.